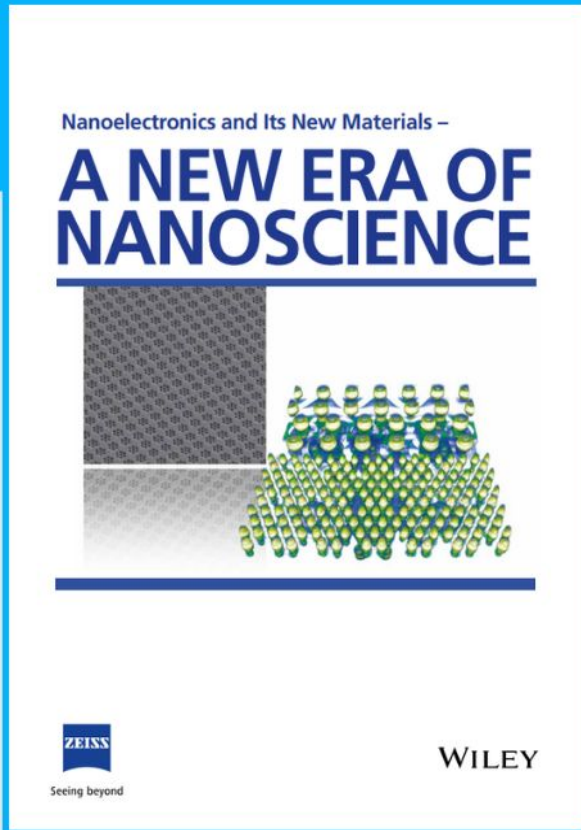




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Defect-Laden MoSe₂ Quantum Dots Made by Turbulent Shear Mixing as Enhanced Electrocatalysts

Chongyang Zhu, Yuan Huang, Feng Xu,* Peng Gao, Binghui Ge, Jing Chen, Haibo Zeng, Eli Sutter, Peter Sutter,* and Litao Sun*

A high density of edge sites and other defects can significantly improve the catalytic activity of layered 2D materials. Herein, this study demonstrates a novel top-down strategy to maximize catalytic edge sites of MoSe₂ by breaking up bulk MoSe₂ into quantum dots (QDs) via “turbulent shear mixing” (TSM). The ultrasmall size of the MoSe₂ QDs provides a high fraction of atoms in reactive edge sites, thus significantly improving the catalytic activities. The violent TSM further introduces abundant defects as additional active sites for electrocatalytic reactions. These edge-proliferated and defect-laden MoSe₂ QDs are found to be efficient electrocatalysts for the hydrogen evolution reaction, and useful as counter electrodes in dye-sensitized solar cells. The work provides a new paradigm for creating edge-proliferated and defect-rich QDs from bulk layered materials.

Layered two-dimensional (LTD) materials have been studied intensely.^[1] Typical LTD materials consist of 2D molecular layers held together by van der Waals forces. Exfoliation of the bulk LTD materials can afford individual layers with useful electronic, optical, and catalytic properties, among others.^[2] Particularly, individual layers of transition-metal dichalcogenides (TMDs) have shown potential in photocatalysis, electrocatalysis, and energy conversion systems,^[3] making them promising candidates for replacing platinum-based catalysts.^[4] It has been reported that the edges of the

crystal layers are favorable catalytic reaction sites of TMDs.^[5] Increasing the density of edge sites can thus enhance the overall reactive activity.^[6] How then to maximize edge sites? We address this question for molybdenum diselenide (MoSe₂) through the use of “turbulent shear mixing”.

MoSe₂, a representative member of the TMDs family, was recently reported to have a higher intrinsic electrical conductivity and lower Gibbs free energy for hydrogen adsorption at the edges when compared to the more extensively studied MoS₂.^[7] Thus, effort has been devoted to obtaining MoSe₂

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electrocatalysts with a high density of active edge sites. For example, Cui and co-workers have prepared MoSe₂ thin films composed of vertically aligned layers with enhanced electrocatalytic activity for the hydrogen evolution reaction (HER) that was attributed to exposed active edges.^[8] Moreover, porous and defect-rich MoSe₂ nanosheets could provide more abundant reactive sites.^[9] Composite structures such as MoSe₂/reduced graphene oxide (rGO), MoSe₂/carbon nanofibers, and MoSe₂/carbon nanotubes,^[10–12] have further been studied with the goal of enhancing electrocatalytic activity. The catalytic properties of MoSe₂ quantum dots (QDs), however, have not been reported so far. Previous works on TMDs have suggested that compared to nanosheets, the QDs have larger surface areas and more edge atoms that could greatly increase their electrocatalytic activity.^[13]

Herein, we have developed a new method that we refer to as “turbulent shear mixing” (TSM) to efficiently break up bulk MoSe₂ crystals into ultrasmall QDs. A disintegration mechanism induced by the high turbulent shear rate is suggested to account for their formation. The resulting small-size MoSe₂ QDs provide a high fraction of exposed atoms on edge sites, which significantly improves their electrocatalytic activity. Moreover, the TSM strategy was efficient in creating defects on the basal planes of MoSe₂ QDs, endowing additional active sites for electrocatalytic reactions. The presence of such a high fraction of edge sites and defects led us to apply these MoSe₂ QDs as an intriguing electrocatalyst for HER and regenerating redox couple in dye-sensitized solar cells (DSSCs).

The typical TSM process for preparing MoSe₂ QDs from bulk MoSe₂ is schematically illustrated in **Figure 1a**. A commercially available kitchen blender is adopted, which consists of six blades in various directions and is fitted with four baffles to suppress rotation of the liquid as a whole and to increase turbulence during the TSM process (Figure S1, Supporting Information). In a typical procedure, MoSe₂ powder, synthesized by the hydrothermal method, was added into the blender containing a mixture of 75 mL water and 75 mL isopropanol for TSM processing (Figure S2, Supporting Information). The selection of solvents used refers to the previous study by Ajayan and co-workers,^[14] in order to keep the surface tension components of solvents well matched with that of MoSe₂ material (Table S1, Supporting Information), which is favorable for the preparation of MoSe₂ QDs by TSM technique and the stability of the targeted dispersion. After a predetermined-time of TSM processing, stable brown MoSe₂ QD (Figure 1a) dispersions can be obtained through centrifugation to remove concomitant MoSe₂ nanosheets.^[2d]

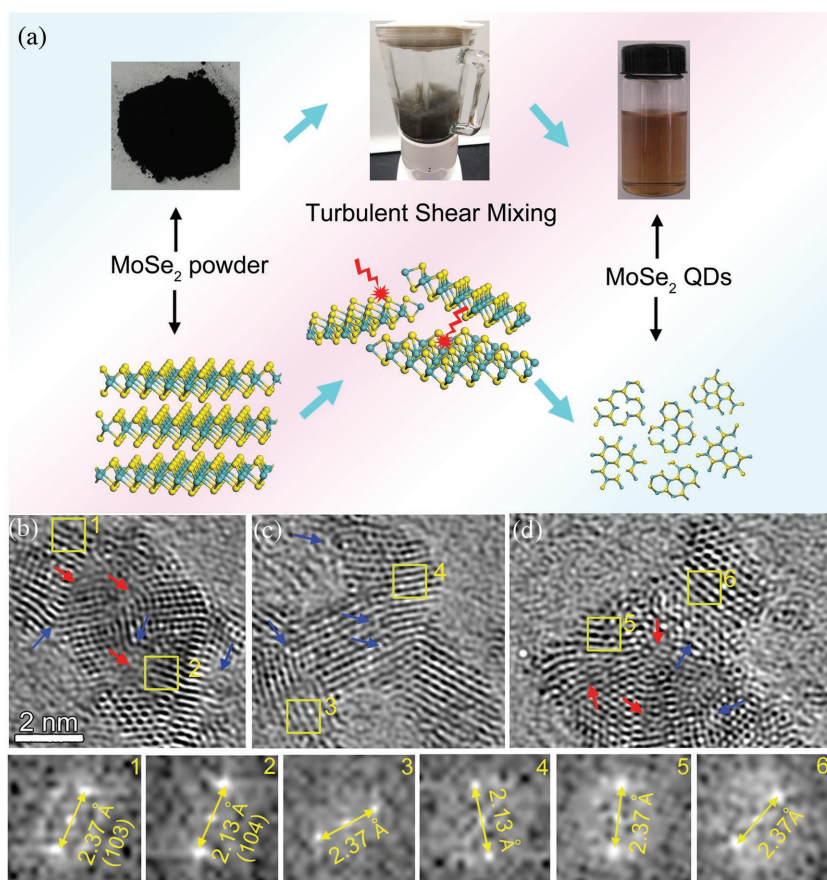


Figure 1. a) Schematic diagram of the TSM process for preparing MoSe₂ QDs from bulk MoSe₂. b–d) Stages of the disintegration process of MoSe₂ at the atomic scale. The HRTEM images are filtered in Fourier space using a mask to select the primary lattice frequencies and to remove the high-frequency noise above the information transfer limit. The lowest row shows fast Fourier transform patterns corresponding to the selected regions in (b–d), revealing the preferential (103) plane for disintegration of MoSe₂ into QDs.

To address the formation mechanism of MoSe₂ QDs by the TSM technique, fluid dynamics involving Reynolds number is invoked to analyze the underlying fluid interactions within a rotating blender.^[2d] Reynolds number can be presented by the formula $Re_{\text{Blade}} = ND^2\rho/\eta$,^[15] where N is the rotor speed, D is blade diameter, ρ and η are the liquid density and viscosity, respectively (see Table S2 in the Supporting Information for more details). When N is near maximum value, the Re_{Blade} can be calculated to be 2.72×10^5 , which is far above the critical value $\approx 10^4$ where turbulence becomes fully developed.^[16] Assuming that all of the input power is dissipated via turbulence, then the mean turbulence shear rate can be expressed as: $\dot{\gamma}_t = \sqrt{P/V\eta}$.^[16] At a maximum N , $P = 400$ W and $V = 0.15$ L, we can obtain a $\dot{\gamma}_t$ of 1.24×10^4 s⁻¹. We believe such a high turbulent shear rate can not only successfully exfoliate LTD nanosheets,^[2d,17] but also accounts for the formation of MoSe₂ QDs via further breaking up MoSe₂ crystal layers.^[18] This disintegrating mechanism is corroborated by transmission electron microscopy (TEM) observation of the ex situ morphology evolution of products at different stages. As shown in Figure S3 (Supporting Information), bulk MoSe₂ was initially exfoliated into dispersive MoSe₂ nanosheets under the high turbulent shear

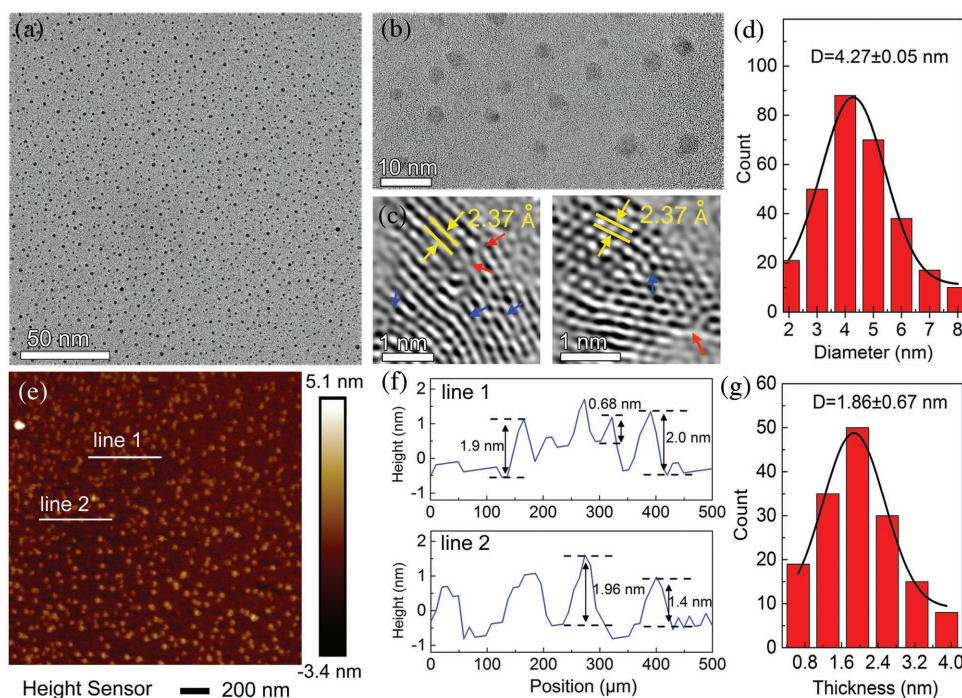


Figure 2. Morphology characterization of MoSe₂ QDs. a, b) Typical TEM bright-field images and c) HRTEM images of as-prepared MoSe₂ QDs. d) Statistical analysis of the size of MoSe₂ QDs measured by TEM. e) AFM image of MoSe₂ QDs. f) Height profiles along the white lines in (e). g) Statistical analysis of the heights of MoSe₂ QDs measured by AFM.

rate. Subsequently, the MoSe₂ nanosheets interspersed with MoSe₂ QDs gradually occurred. This observation of intermediate process provides a solid proof that the QDs originated from the initially exfoliated nanosheets. Further prolonging the TSM process, abundant MoSe₂ QDs with ultrasmall sizes are finally formed. In addition to MoSe₂ QDs, this disintegration mechanism also shows the universality in preparing QDs of other LTD materials (Figure S4, Supporting Information). High-resolution TEM (HRTEM) images (Figure 1b–d) of intermediate products are further acquired with disordered lattice fringes (marked by arrows), revealing MoSe₂ nanosheets could not maintain ideal 2D crystal structure under the high turbulent shear rate, instead were contorted to a highly defective structure,^[6b] and then broken up into small QDs. By investigating the crystal structure of edges, we further found that MoSe₂ nanosheets preferentially disintegrate from (103) planes, which is also a preferred crystal plane during the growth of MoSe₂.

The structure of the as-obtained MoSe₂ QDs is characterized by TEM. **Figure 2a** evidences a large quantity of QDs with a mean size of 4.3 nm. HRTEM images show lattice fringes of these QDs are 2.37 Å, corresponding to the (103) plane of hexagonal MoSe₂. It is worth to note that discontinuous (red arrows) and contorted (blue arrows) lattice fringes are also clearly observed, indicating that the TSM technique can be used for preparing defect-laden QDs.^[6b] This differs from the conventional ultrasonication method that generates QDs with high crystallization.^[13b,19] Further morphology and thickness of MoSe₂ QDs were investigated by atomic force microscopy (AFM) measurement (Figure 2e–g). Height profiles reveal a thickness of 0.68–2 nm (Figure 2f), about 1–3 layers, since the thickness of single-layer MoSe₂ is about

0.65 nm (Figure S5, Supporting Information).^[19a] This result is corroborated by statistical histogram in Figure 2g with a mean thickness of 1.86 nm. Compared to the bulk counterpart, the ultrasmall and defect-laden MoSe₂ QDs can provide a higher fraction of catalytic atoms on both basal planes and edges.

The surface chemical composition and valence states of MoSe₂ QDs was confirmed by the X-ray photoelectron spectroscopy (XPS). As shown in **Figure 3a,b**, the peaks around 228.9 and 232.2 eV correspond to Mo 3d_{5/2} and Mo 3d_{3/2}, respectively, while the peaks at 54.5 and 55.3 eV can be attributed to Se 3d_{5/2} and Se 3d_{3/2} orbits, which are in good agreement with the binding energies of Mo⁴⁺ and Se²⁻ of MoSe₂.^[7a] No signal from the Mo⁶⁺ was observed, indicating that there is no obvious oxidation of MoSe₂ QDs.^[19] Figure 3c presents the Raman spectrum of MoSe₂ QDs. Two distinct Raman peaks at 238 and 285 cm⁻¹ correspond to the out-of-plane (A_g¹) and in-plane (E_{2g}¹) Mo–Se vibrations of MoSe₂ QDs, respectively,^[8] as illustrated in Figure S6 (Supporting Information). A_g¹ is typically preferentially excited for edge-terminated MoSe₂, while E_{2g}¹ is preferentially excited for terrace-terminated MoSe₂.^[8] Compared with bulk MoSe₂, MoSe₂ QDs show a redshift by 5.4 cm⁻¹ in E_{2g}¹ mode, analogous to that observed in boron nitride (BN) QDs due to small lateral dimensions.^[20] Moreover, the E_{2g}¹ peak in the MoSe₂ QDs is also less pronounced (intensity is only 13% of A_g¹ peak) and broad. This means that the A_g¹ mode is preferentially excited in the as-prepared MoSe₂ QDs, confirming that the MoSe₂ QDs have more exposed catalytic edge sites.^[8]

Further characterizations are performed by measuring the absorption spectrum and photoluminescence (PL)

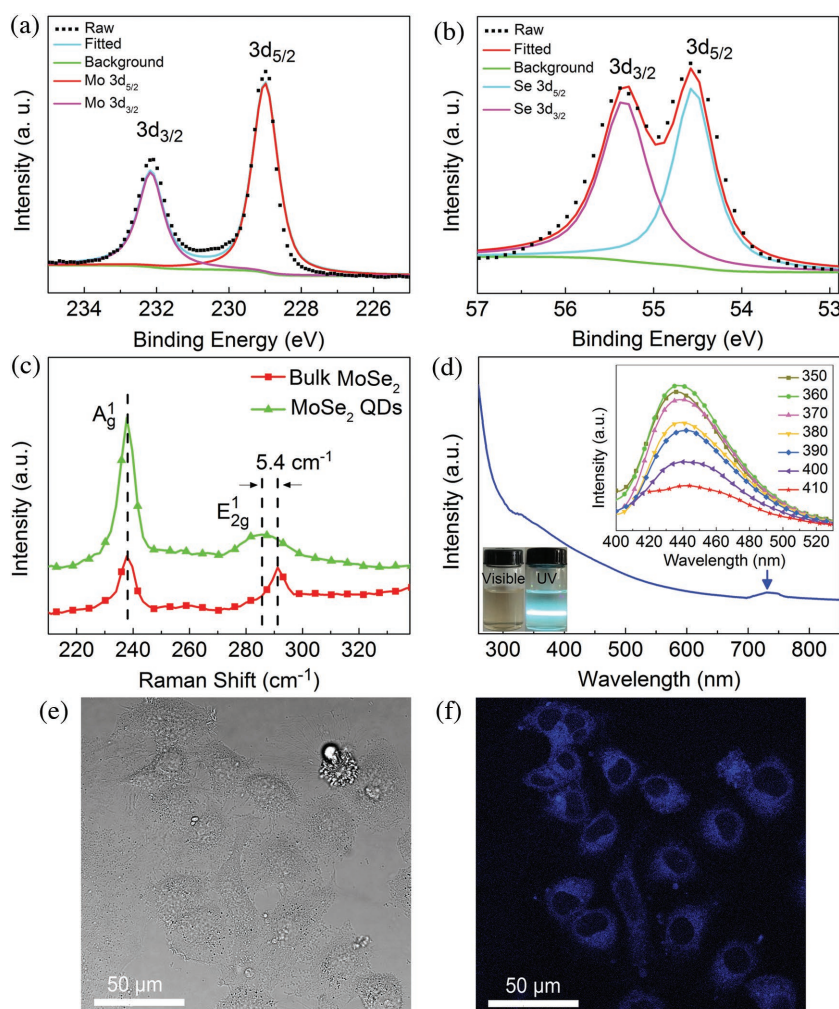
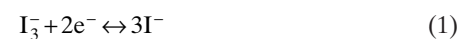


Figure 3. High-resolution XPS spectra of a) Mo 3d and b) Se 3d core levels. c) Raman spectrum of MoSe₂ QDs and bulk MoSe₂. d) UV-vis absorption spectrum of MoSe₂ QD dispersions. Inset: PL spectra of MoSe₂ QD dispersions under different excitation wavelengths, and optical photograph of MoSe₂ QD dispersions under visible and UV light. e) Bright-field image and f) corresponding confocal laser scanning microscopy image of HeLa living cells incubated with MoSe₂ QDs.

spectra of MoSe₂ QDs. Obviously, MoSe₂ QDs show a broad absorbance pattern in the visible region and near-infrared (NIR) band (Figure 3d). Strong fluorescence also can be seen from the optical photograph under 365 nm UV illumination (inset in Figure 3d). The small peak at 745 nm (≈ 1.66 eV) is generally ascribed to excitonic emission from MoSe₂, which is blueshifted compared with single-layer nanosheets (1.57 eV).^[21] This is mainly attributed to a quantum size confinement effect, i.e., the optical absorption exhibiting a strong blueshift when the lateral dimensions of nanomaterials are reduced to below 50 nm.^[22] Such effect is further evidenced in PL spectra (inset in Figure 3d) of MoSe₂ QDs, which show a characteristic emission peak at 445 nm under excitation of 360 nm wavelength. The emission is strongly blueshifted compared to that for single-layer MoSe₂ nanosheet.^[21] With increasing the excitation wavelength, the emission peak shifts to the red and remain obvious intensity at 400 nm excitation wavelength. Such strong excitation-dependent features in PL reveal the polydispersity of MoSe₂ QDs,^[22] which ensures the

remarkable fluorescence of HeLa living cells when incubated with MoSe₂ QDs (Figure 3e,f). Generally, the polydispersity is owing to the difference in the particle size and the presence of surface trap states of defective MoSe₂ QDs.^[22,23]

As typical applications, we have demonstrated the defect-laden MoSe₂ QDs as enhanced electrocatalysts toward the reduction of I₃⁻ in DSSCs and for HER as well. The catalytic activities toward the reduction of I₃⁻ are evaluated by cyclic voltammetry (CV) measurements in Figure 4a and Figure S7 (Supporting Information). Two pairs of typical oxidation and reduction peaks (Ox-1/Red-1, Ox-2/Red-2) can be well distinguished, corresponding to the reaction of Equations (1) and (2),^[24] respectively. Since the catalysts in DSSCs are responsible for catalyzing reduction of I₃⁻ to I⁻, the characteristics of the left pair (Ox-1/Red-1) are at the main concern of our analysis.



Generally, high current densities and low separation between Red-1 and Ox-1 peaks (E_{pp}) indicate excellent catalytic activity toward reduction of I₃⁻.^[25] From Table 1, MoSe₂ QD electrode has a higher cathodic current density and a smaller E_{pp} value of 0.32 V than bulk MoSe₂ and Pt electrodes, suggesting a faster catalytic rate for I⁻ regeneration on the surface of MoSe₂ QD electrode.^[25] To further gain insight into the charge transfer process at

the electrode–electrolyte interface, electrochemical impedance spectra measurements are also performed (Figure 4b and Table 1).^[26] All three electrodes have nearly the same absolute series resistance (R_s), revealing a negligible role of R_s on differences in the electrocatalytic performance of different electrodes. However, the MoSe₂ QD electrode exhibits a lower charge transfer resistance (R_{ct}) of 5.46 Ω than 9.41 Ω of bulk MoSe₂ electrode, implying faster charge transport at the MoSe₂ QD electrode–electrolyte interface. Generally, faster charge transport means higher exchange current density, which is evidenced by the Tafel polarization curves (Figure S8, Supporting Information).

The excellent catalytic activities of MoSe₂ QDs make them promising candidates for replacing Pt catalyst, which has a low abundance on the earth and is of high cost.^[24] Figure 4c compares the photovoltaic performance of DSSCs assembled with various counter electrodes (CEs). When bulk MoSe₂ is used as CE, the open-circuit voltage (V_{oc}), short-circuit current density (J_{sc}), fill factor (FF), and power conversion

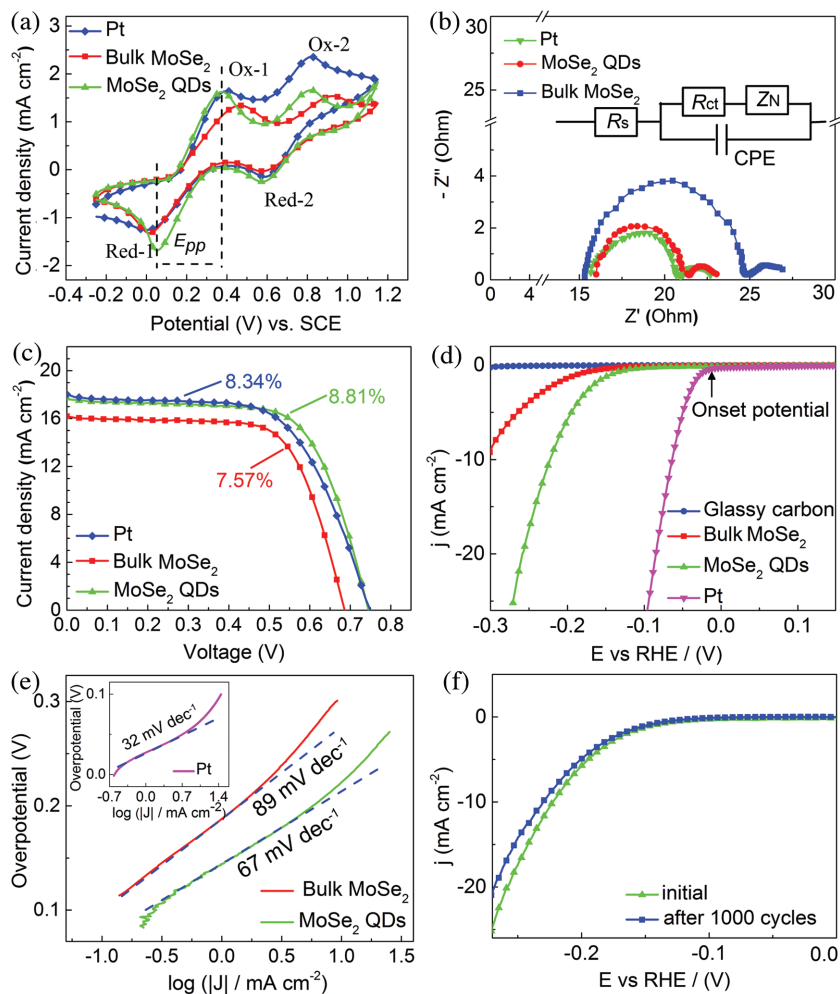


Figure 4. Electrocatalysis applications of MoSe₂ QDs in DSSCs (a–c) and HER (d–f). a) CV curves of Pt, MoSe₂ QDs, and bulk MoSe₂ CEs, obtained in acetonitrile solution containing 10.0×10^{-3} M LiI, 1.0×10^{-3} I₂, and 0.1 M LiClO₄ (scan rate: 50 mV s^{-1}). b) Electrochemical impedance spectra of above three CEs, obtained with two identical electrodes in the same electrolyte as that used in DSSCs. Inset shows the equivalent circuit used in DSSCs. c) Photocurrent density–voltage (*j*–*V*) curves of DSSCs constructed using above three electrodes. d) LSV polarization curves and e) the corresponding Tafel plots of commercial Pt, bulk MoSe₂, and MoSe₂ QDs, obtained in 0.5 M H₂SO₄ electrolyte at a scan rate of 2 mV s^{-1} . f) LSV polarization curves for MoSe₂ QD catalysts before and after 1000 times of CV cycles.

efficiency (PCE) are 0.70 V, 16.10 mA cm^{-2} , 0.68, and 7.57%, respectively (Table 1). This PCE value is apparently lower than 8.34% achieved from Pt CE. However, by replacing the bulk MoSe₂ CE with MoSe₂ QD CE, the PCE of the corresponding DSSC increases to 8.81%. Such impressive PCE not only can rival that of Pt CE, but also is outstanding among the LTD CEs (Table S3, Supporting Information).

For the application of HER, catalytic activities of MoSe₂ QDs as well as bulk MoSe₂ and Pt, are probed by linear

sweep voltammetry (LSV) in 0.5 M H₂SO₄ using a three-electrode configuration. As shown in Figure 4d, the Pt catalyst exhibits extremely high HER catalytic activity with a near zero onset potential (i.e., the potential at which the HER reactivity begins,^[27] as marked in Figure 4d) and large current density. Contrarily, bulk MoSe₂ shows very weak HER performance with a low cathodic current density and high onset potential. Significant H₂ evolution ($J = 10 \text{ mA cm}^{-2}$) is not achieved until -300 mV versus reversible hydrogen electrode. However, by replacing the bulk MoSe₂ with MoSe₂ QDs, the onset of catalytic activity shifts to a much more positive potential -124 mV , beyond which the cathodic current increases rapidly under more negative potentials. In addition, significant H₂ evolution is also found at a lower voltage of -221 mV ($J = 10 \text{ mA cm}^{-2}$), indicating superior electrocatalytic activity of MoSe₂ QDs than bulk MoSe₂. Figure 4e presents Tafel slopes of different electrodes, which is an intrinsic property of electrocatalysts and is typically determined by the rate-limiting step of the HER.^[28] It can be determined by Tafel plots where their linear portions are fit to the Tafel equation ($\eta = b \times \log j + a$, in which *j* is the current density and *b* is the Tafel slope). From Figure 4e, Tafel slopes of Pt, bulk MoSe₂, and MoSe₂ QDs are 32, 89, and 67 mV dec^{-1} , respectively. The smaller Tafel slope of MoSe₂ QDs than bulk MoSe₂ is advantageous for practical applications since it will lead to a faster increment of HER rate with increasing overpotential.^[11b] Besides the HER activity, the durability is another significant quality for an advanced electrocatalysts.

Figure 4f shows the comparison polarization curves for the MoSe₂ QD catalysts before and after 1000 cycles. Slight activity loss is observed, which may be caused by the mild oxidation of MoSe₂ QDs into MoO₃ (Figure S9, Supporting Information), or the remaining H₂ bubbles on the surface of the electrode that hinder the HER.^[29]

Table 2 compares the HER performance of various MoSe₂ nanostructures. Obviously, MoSe₂ QD shows excellent HER activity among the undoped MoSe₂ catalysts such as MoSe₂ nanosheets,^[30] porous MoSe₂ nanosheets,^[9] and

Table 1. Parameters of electrochemical and photovoltaic performance using different CEs.

CEs	V_{oc} [V]	J_{sc} [mA cm^{-2}]	FF [%]	PCE [%]	R_s [Ω]	R_{ct} [Ω]	E_{pp} [mV]
Pt	0.75	17.83	0.63	8.34	15.66	4.01	440
MoSe ₂ QDs	0.74	17.56	0.67	8.81	15.96	5.46	320
Bulk MoSe ₂	0.70	16.10	0.68	7.57	15.35	9.41	480

Table 2. Comparison of HER performance of various MoSe₂ nanostructures in 0.5 M H₂SO₄.

MoSe ₂ nanostructures	Method	Onset potential ^{a)} [V]	Tafel slope [mV dec ⁻¹]	Ref.
MoSe ₂ QDs	TSM	-0.12	67	Our work
Porous MoSe ₂ nanosheet	Liquid exfoliation	-0.07	80	[9]
MoSe ₂ nanosheet	Colloidal synthesis	-0.17	98	[30]
MoSe ₂ film	CVD	-0.2	105–120	[8]
S-doped MoSe ₂ nanosheet	Reflux method	-0.09	60	[29]
MoSe ₂ nanosheet/rGO	Hydrothermal	-0.05 to -0.125	67–69	[7a,10b]
MoSe ₂ nanosheet/carbon fiber	Solvothermal	-0.07 to -0.145	69–76	[11a]
MoSe ₂ film/carbon fiber	CVD	-0.11	59.8	[11b]
MoSe ₂ nanosheet/carbon nanotube	Solvothermal	-0.07	58	[12]

^{a)}Onset potential: the potential at which the HER reactivity begins.

MoSe₂ films.^[8] Even, our MoSe₂ can rival the S-doped MoSe₂ nanosheets^[29] or MoSe₂-based composites.^[7a,10b,11,12] The excellent catalytic activity of defect-laden MoSe₂ QDs can be attributed to two advantageous peculiarities. First, compared with their bulk counterpart, the ultrasmall size of MoSe₂ QDs provides an enhanced edge to basal plane ratio, hence resulting in higher catalytic activities from reactive edges.^[31] Second, a large amount of defect sites have been created on the basal planes of MoSe₂ QDs, which is also favorable for catalytic reactions.^[6b,9] Finally, it is worth noting that the HER performance of MoSe₂ QDs can be further improved through optimizing electrode mass/area or by mixing in carbon material such as graphene to improve electrical properties of the catalyst.^[32]

In summary, we have demonstrated a novel “turbulent shear mixing” method to successfully engineer the nanostructure of MoSe₂ catalysts with prolific catalytic edge and basal-plane sites. With this approach, ultrasmall MoSe₂ QDs with a mean lateral size of 4.3 nm can be prepared that provide a high fraction of atoms in edge sites, which significantly improves the catalytic activity of the QDs. Moreover, the TSM was also found to generate abundant defective sites in the MoSe₂ QDs via the violent disintegration process, producing additional catalytic active sites. Thanks to these unique properties, the defect-laden MoSe₂ QDs have shown excellent electrocatalysis in both HER and DSSCs. We believe the current study provides a new paradigm for engineering LTD materials with prolific active sites for enhanced electrocatalysis.

Supporting Information

Supporting Information is available from the Wiley Online Library or from the author.

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Conflict of Interest

The authors declare no conflict of interest.

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